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(12) **United States Design Patent**
Kawase et al.

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(54) **SEMICONDUCTOR DEVICE**
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Tokyo (JP)

(Continued)

(**) Term: **14 Years**

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Primary Examiner — Elizabeth J Oswecki

(30) **Foreign Application Priority Data**

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(51) **LOC (10) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(57) **CLAIM**

The ornamental design for a semiconductor device, as shown and described.

(58) **Field of Classification Search**
USPC D13/110, 182, 184; 361/713, 728, 736,
361/760, 761, 775, 679.01, 820; 257/666,
257/668, 678, 690; 324/71.5, 252; 174/250,
174/253; 438/64, 65, 66
See application file for complete search history.

DESCRIPTION

FIG. 1 is a front, top and right side perspective view of a semiconductor device, showing our new design;
FIG. 2 is a rear, top and left side perspective view thereof;
FIG. 3 is a front elevational view thereof;
FIG. 4 is a rear elevational view thereof;
FIG. 5 is a left side elevational view thereof;
FIG. 6 is a right side elevational view thereof;
FIG. 7 is a top plan view thereof;
FIG. 8 is a bottom plan view thereof;
FIG. 9 is a perspective view shown in a used condition with a device shown in broken lines; and,
FIG. 10 is a front view shown in a used condition with a device shown in broken lines.

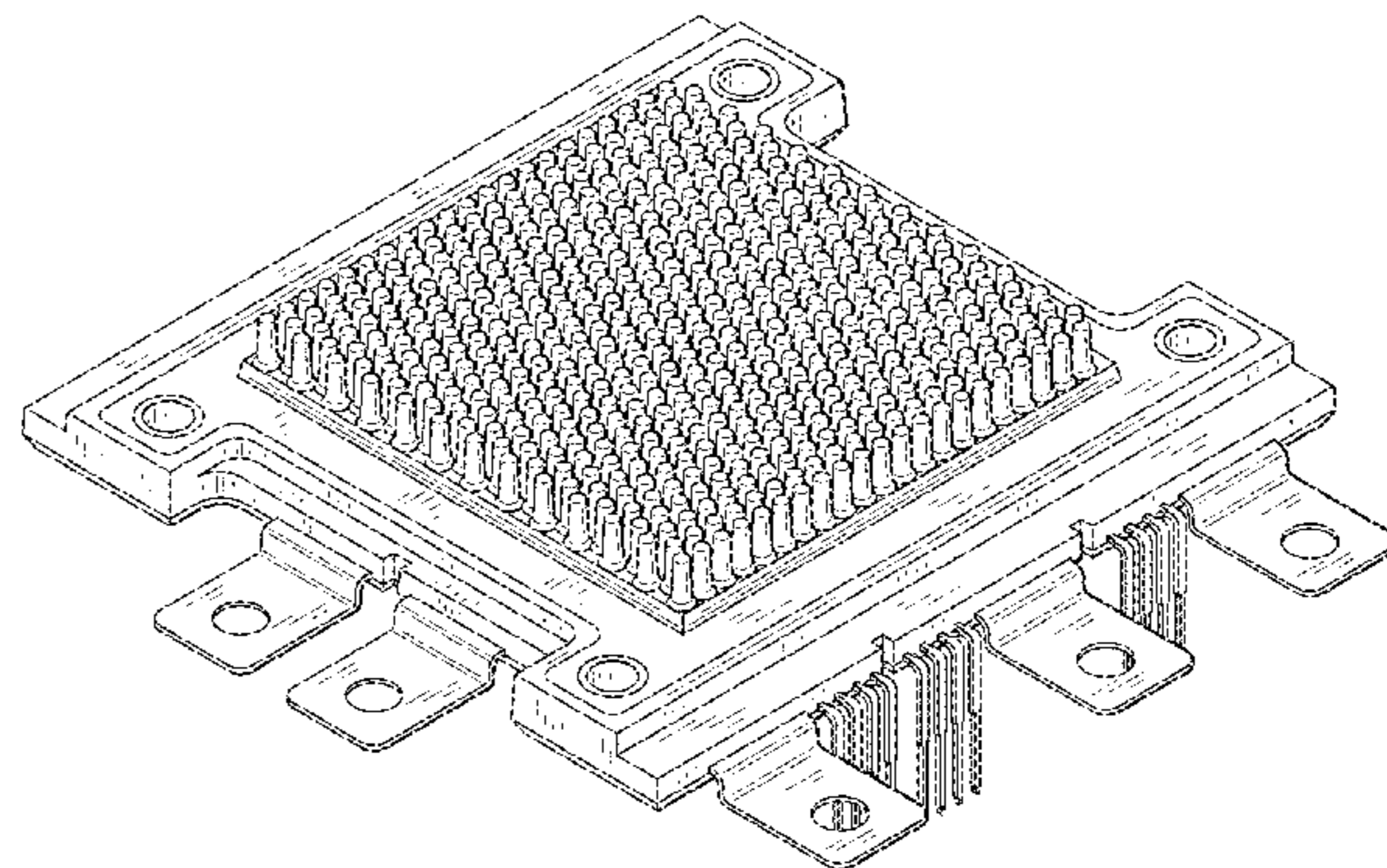
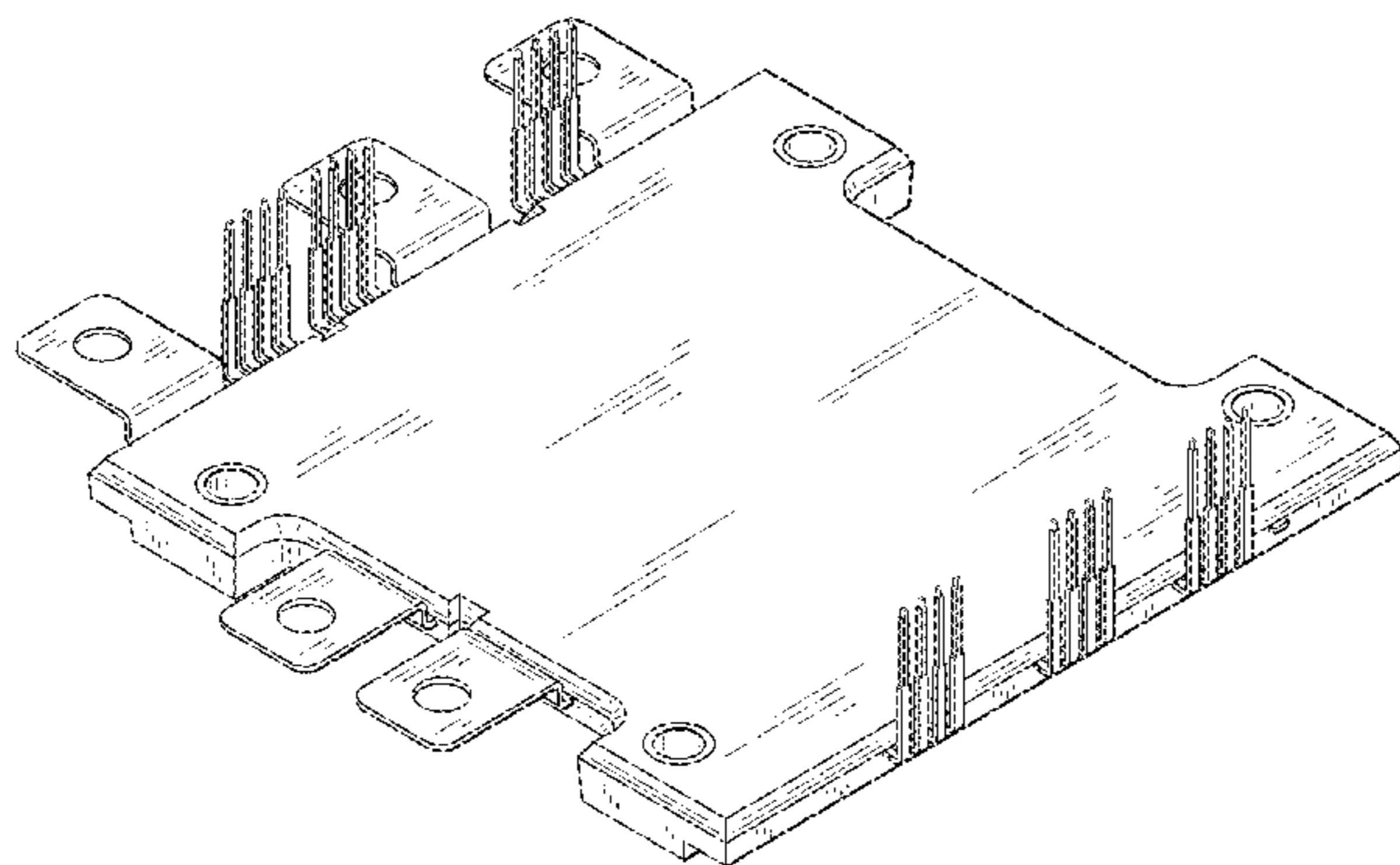
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The broken lines shown in the drawings represent portions of the semiconductor device that form no part of the claimed design.

1 Claim, 8 Drawing Sheets



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FIG. 1

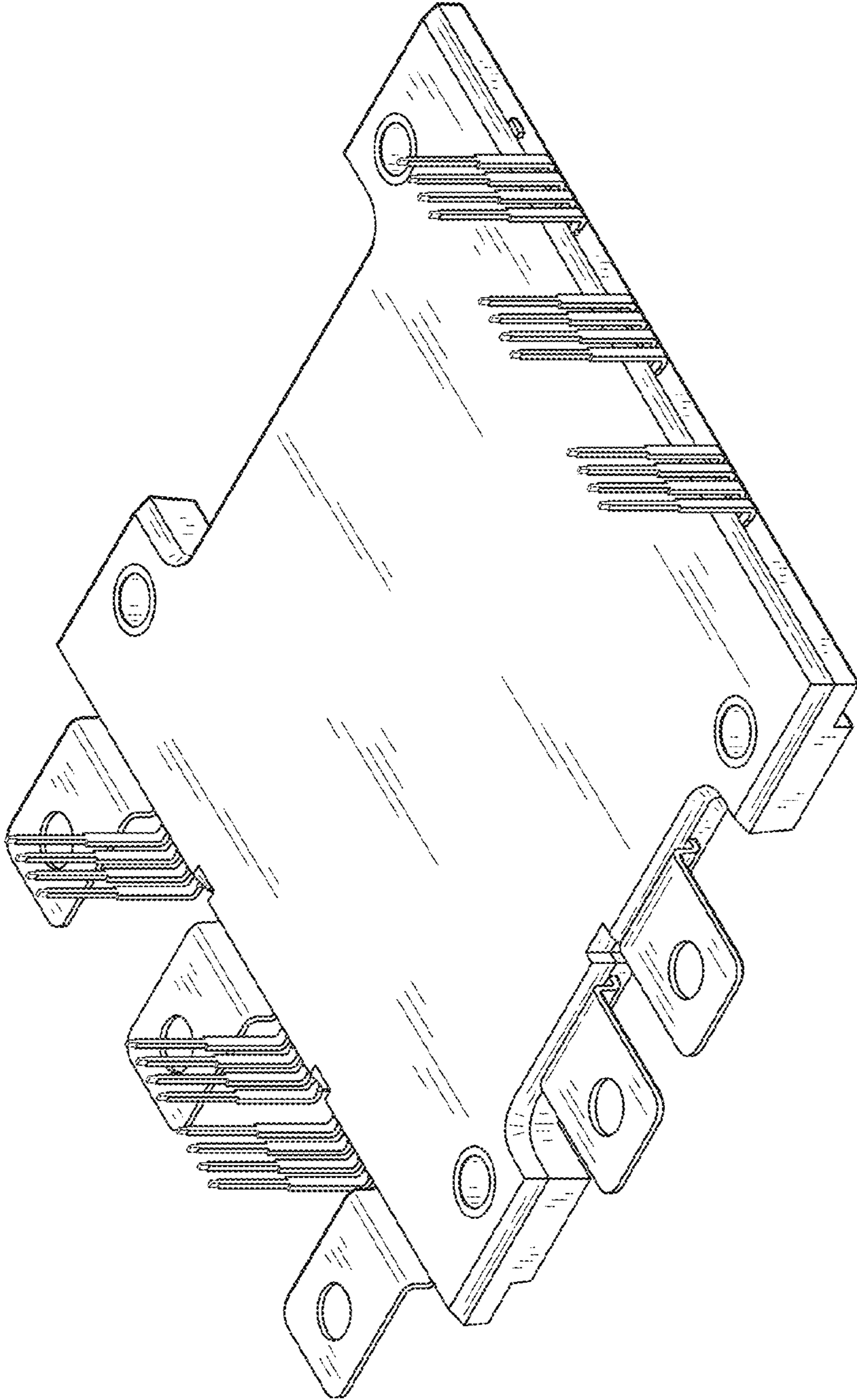


FIG. 2

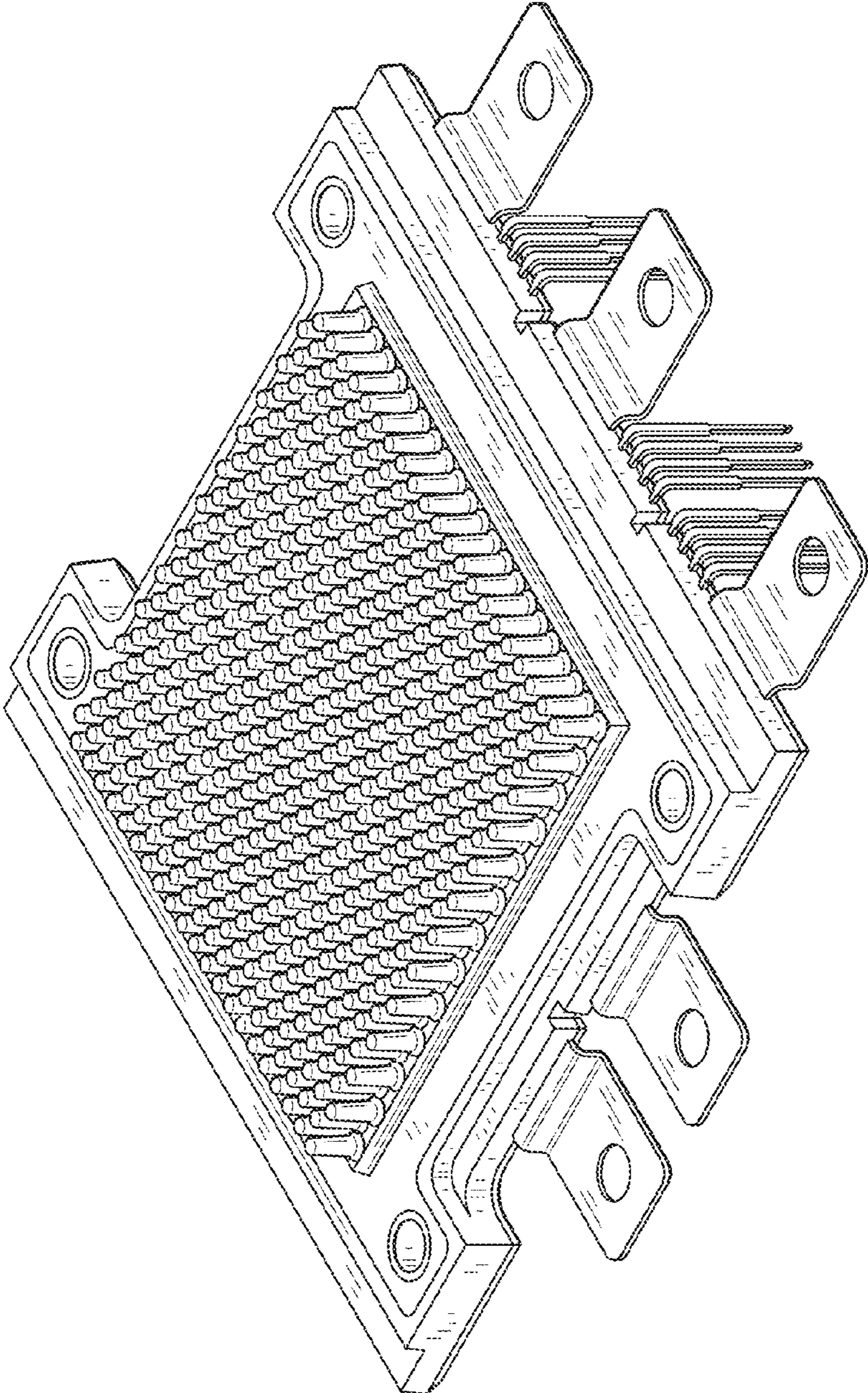


FIG. 3

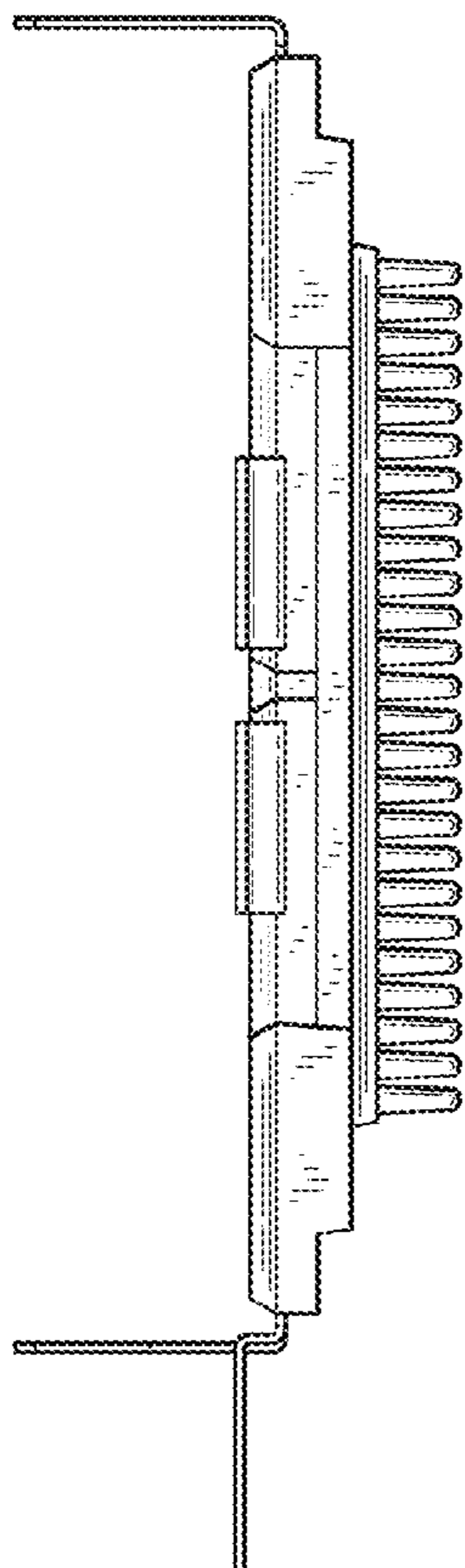


FIG. 4

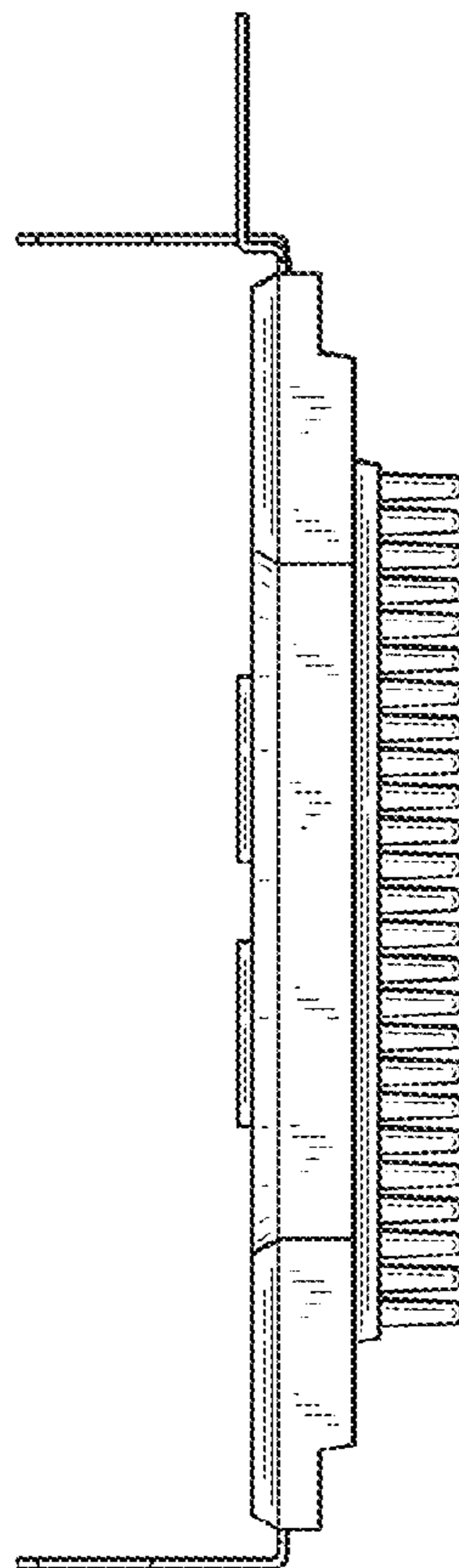


FIG. 5

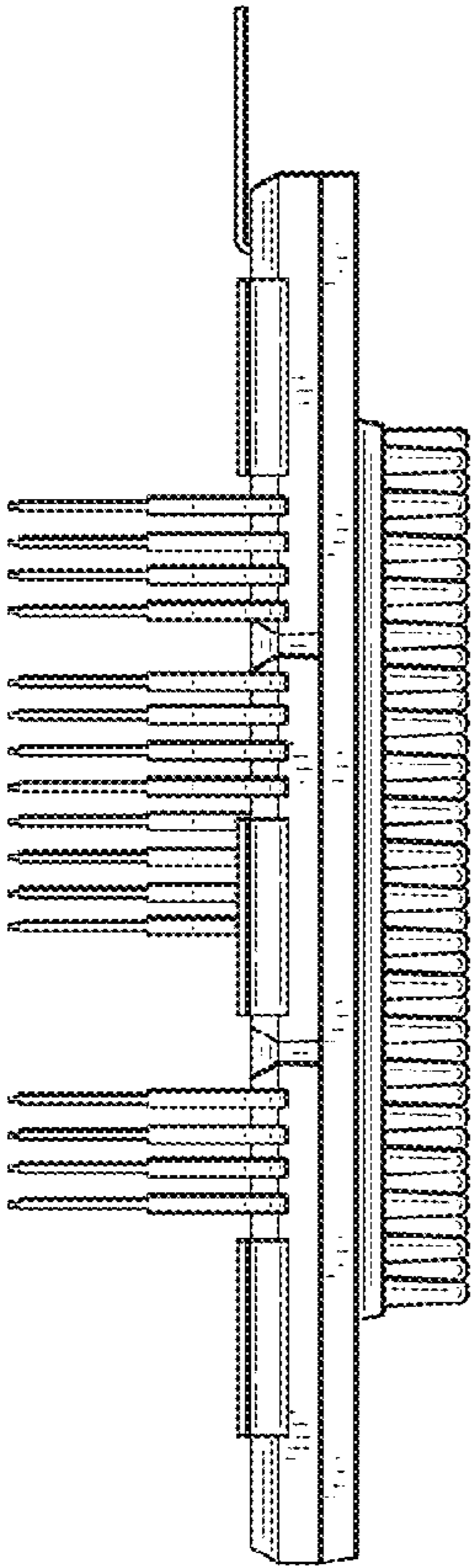


FIG. 6

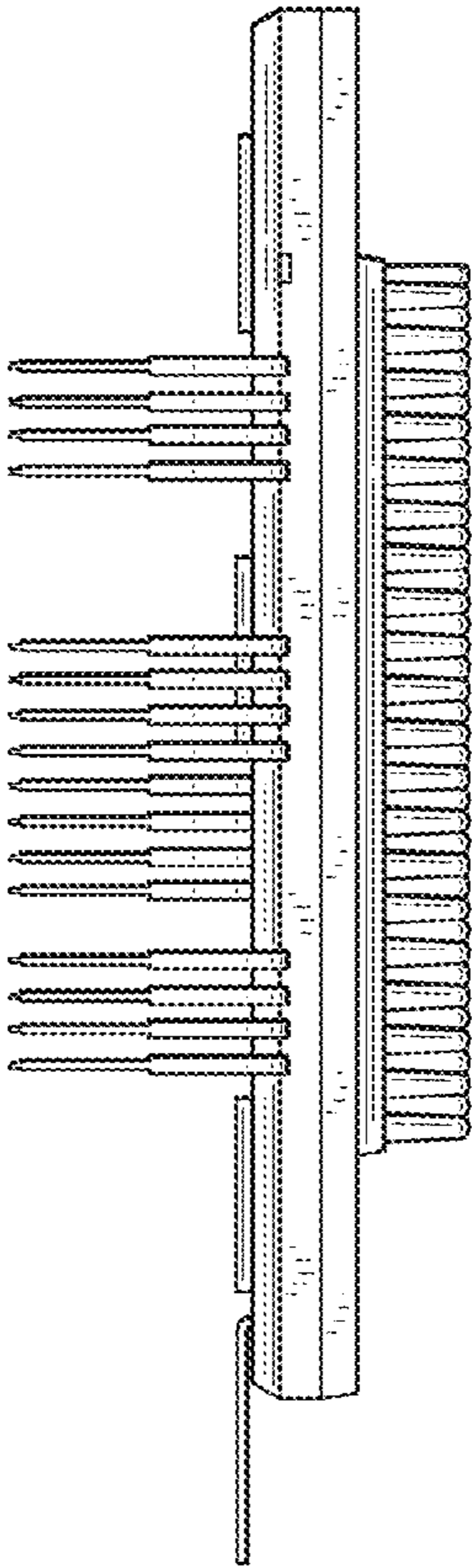


FIG. 7

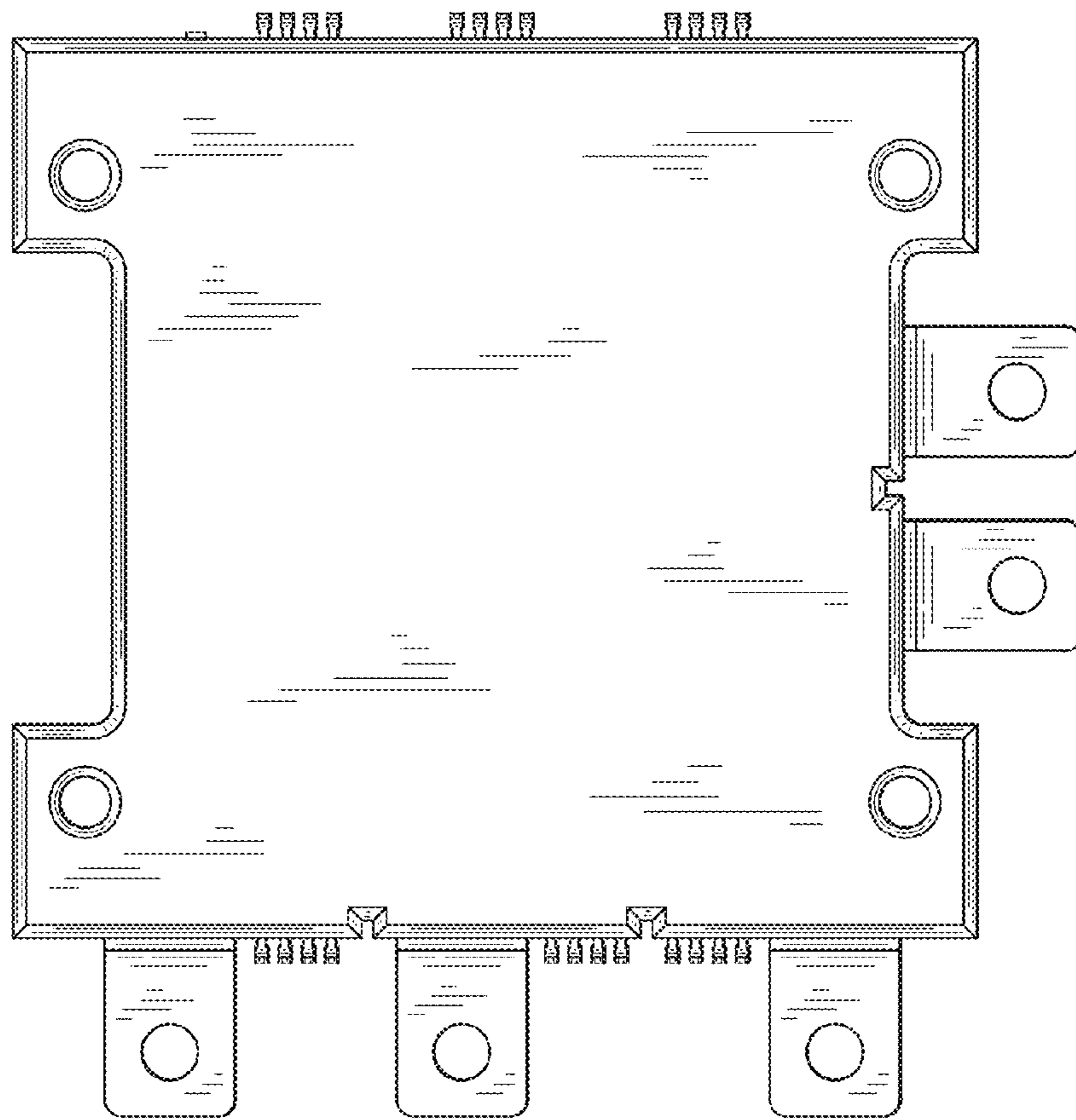


FIG. 8

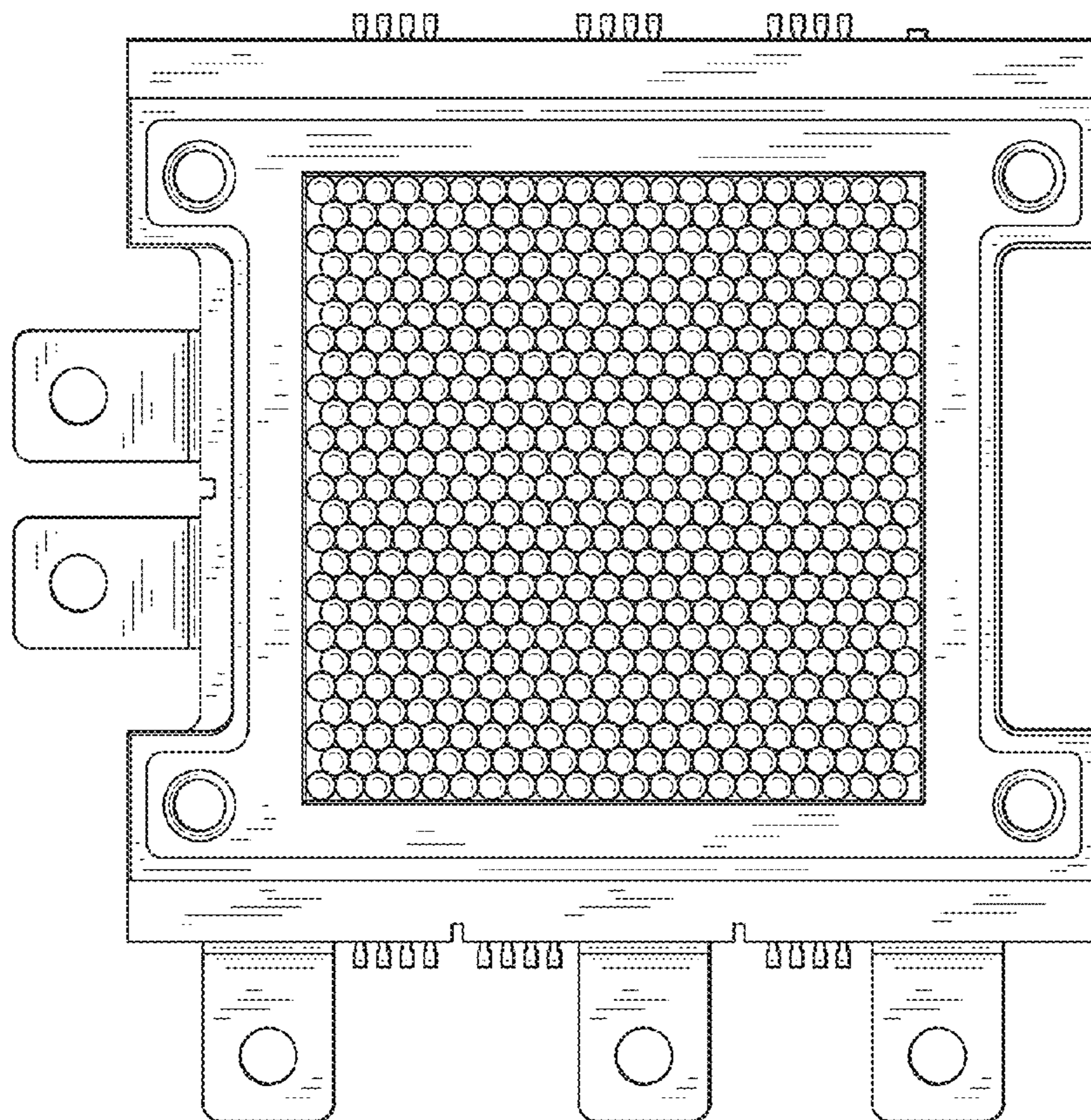


FIG. 9

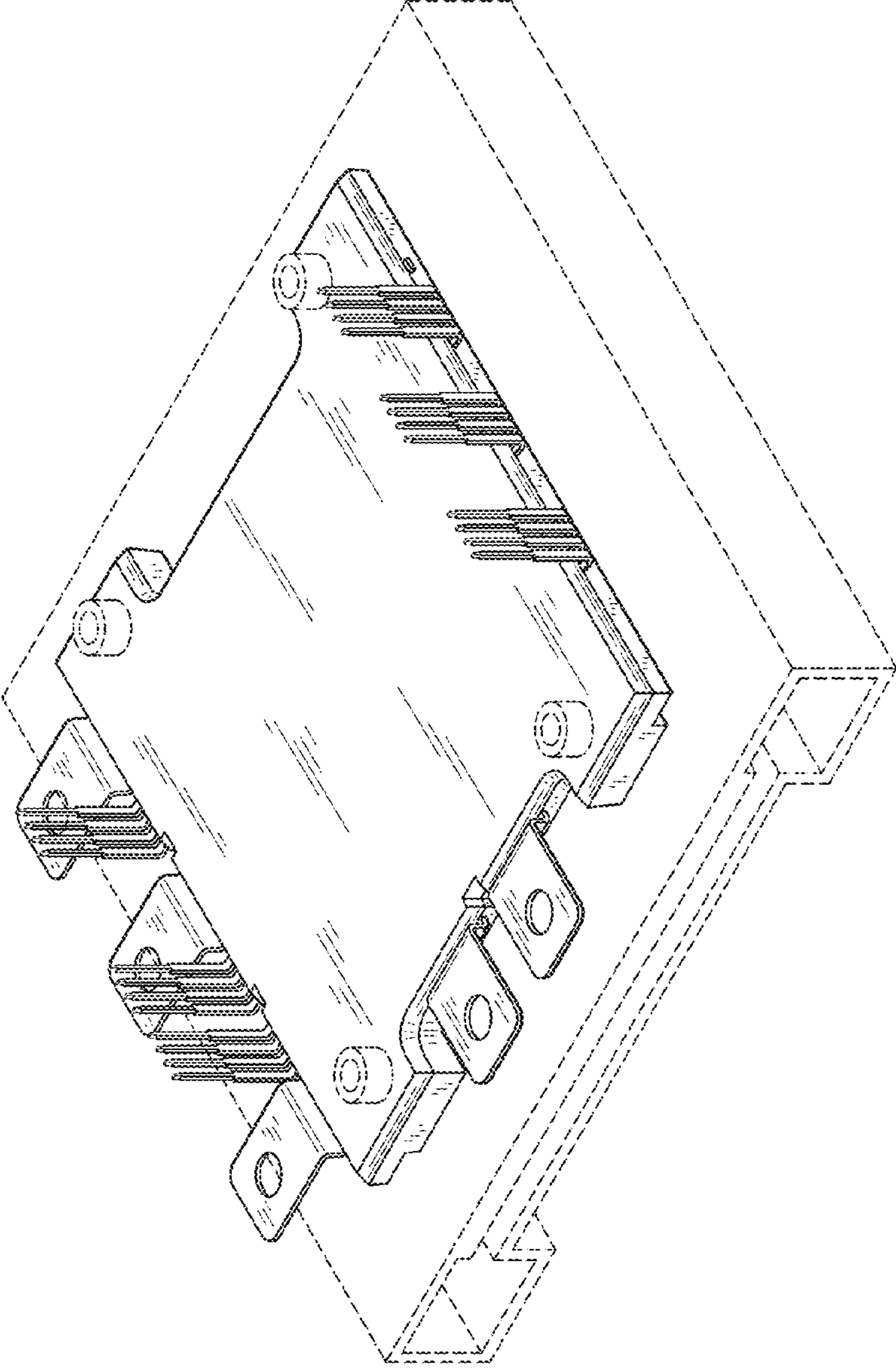


FIG. 10

